

IN THE CLAIMS

Please amend the claims as follows:

Claim 1-13 (Canceled).

Claim 14 (Original): A method of manufacturing a semiconductor device comprising:

forming a germanium low-concentration region containing germanium of low concentration and a germanium high-concentration region containing germanium of high concentration in a semiconductor region containing at least silicon,

forming P-type and N-type diffusion layers in the semiconductor region with a boundary region between the above diffusion layers being set in the germanium high-concentration region, and

forming a silicide film which extends from the N-type diffusion layer over to the boundary region and the P-type diffusion layer.

Claim 15 (Original): The method according to claim 14, wherein the germanium low-concentration region and the germanium high-concentration region are formed by oxidizing a selected portion of the semiconductor region when the semiconductor region contains germanium.

Claim 16 (Original): The method according to claim 15, wherein the germanium high-concentration region is formed in the selected portion and the germanium low-concentration region is formed in a portion other than the selected portion.

Claim 17 (Original): The method according to claim 14, wherein the P-type diffusion layer is formed in the germanium high-concentration region.

Claim 18 (Original): The method according to claim 14, wherein a natural oxide film is removed before the silicide film is formed.

Claim 19 (Original): The method according to claim 18, wherein an etchant containing hydrofluoric acid is used to remove the natural oxide film.

Claim 20 (Original): A method of manufacturing a semiconductor device comprising:

forming a P-type semiconductor region in which a first transistor is formed and an N-type semiconductor region in which a second transistor is formed on a substrate,

forming a semiconductor film containing at least silicon on the P-type and N-type semiconductor regions,

forming a germanium low-concentration region containing germanium of low concentration on the P-type semiconductor region and a germanium high-concentration region containing germanium of high concentration on the N-type semiconductor region in the semiconductor region,

patterning the semiconductor region into an electrode pattern of the first transistor on the P-type semiconductor region and into an electrode pattern of the second transistor on the N-type semiconductor region,

respectively forming N-type and P-type diffusion layers in the P-type and N-type semiconductor regions and disposing the P-type and N-type diffusion layers in the electrode patterns with a boundary region between the above diffusion layers being set in the germanium high-concentration region, and

forming a silicide film on the N-type diffusion layer in the P-type semiconductor region and the P-type diffusion layer in the N-type semiconductor region, the silicide film

being formed to extend from the N-type diffusion layer in the electrode pattern over to the boundary region and the P-type diffusion layer.